

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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# General purpose (dual digital transistors) **UMH7N**

#### Feature

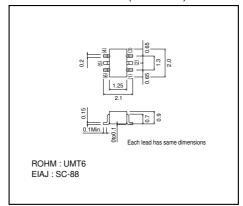
1) Includes two DTC143T transistors in a single UMT package.

## ● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vcвo	50	V	
Collector-emitter voltage	Vceo	50	V	
Emitter-base voltage	VEBO	5	V	
Collector current	lc	100	mA	
Collector power dissipation	Pc	150 (TOTAL)	mW *1	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55~+150	°C	

<sup>\*1 120</sup>mW per element must not be exceeded.

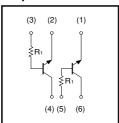
#### ●External dimensions (Units : mm)



# ● Package, marking, and Packaging specifications

Part No.	UMH7N
Package	UMT6
Marking	H7
Code	TR
Basic ordering unit (pieces)	3000

## ●Equivalent circuit



# ● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	50	-	-	V	Ic=50μA
Collector-emitter breakdown voltage	BVcEo	50	-	-	V	Ic=1mA
Emitter-base breakdown voltage	BV <sub>EBO</sub>	5	-	-	V	Iε=50μA
Collector cutoff current	Ісво	-	-	0.5	μΑ	VcB=50V
Emitter cutoff current	IEBO	-	-	0.5	μΑ	V <sub>EB</sub> =4V
DC current transfer ratio	hre	100	250	600	-	VcE/Ic=5V/1mA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	-	-	0.3	V	Ic/I <sub>B</sub> =5mA/0.25mA
Input resistance	R <sub>1</sub>	3.29	4.7	6.11	kΩ	-

